

BT169 series

Thyristors logic level

Rev. 5 — 30 September 2011

Product data sheet

1. Product profile

1.1 General description

Passivated, sensitive gate thyristors in a SOT54 plastic package.

1.2 Features and benefits

- Designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.3 Applications

- General purpose switching and phase control applications.

1.4 Quick reference data

- $V_{\text{DRM}}, V_{\text{RRM}} \leq 200 \text{ V}$ (BT169B)
- $V_{\text{DRM}}, V_{\text{RRM}} \leq 400 \text{ V}$ (BT169D)
- $V_{\text{DRM}}, V_{\text{RRM}} \leq 600 \text{ V}$ (BT169G)
- $I_{\text{T(RMS)}} \leq 0.8 \text{ A}$
- $I_{\text{T(AV)}} \leq 0.5 \text{ A}$
- $I_{\text{TSM}} \leq 8 \text{ A}$

2. Pinning information

Table 1. Discrete pinning

| Pin | Description | Simplified outline | Symbol |
|-----|-------------|----------------------|-----------------------------|
| 1 | anode (a) | <p>SOT54 (TO-92)</p> | <p>A — G — K sym037</p> |
| 2 | gate (g) | | |
| 3 | cathode (k) | | |

3. Ordering information

Table 2. Ordering information

| Type number | Package | | Version |
|-------------|---------|---|---------|
| | Name | Description | |
| BT169B | - | plastic single-ended leaded (through hole) package; 3 leads | SOT54 |
| BT169D | | | |
| BT169G | | | |

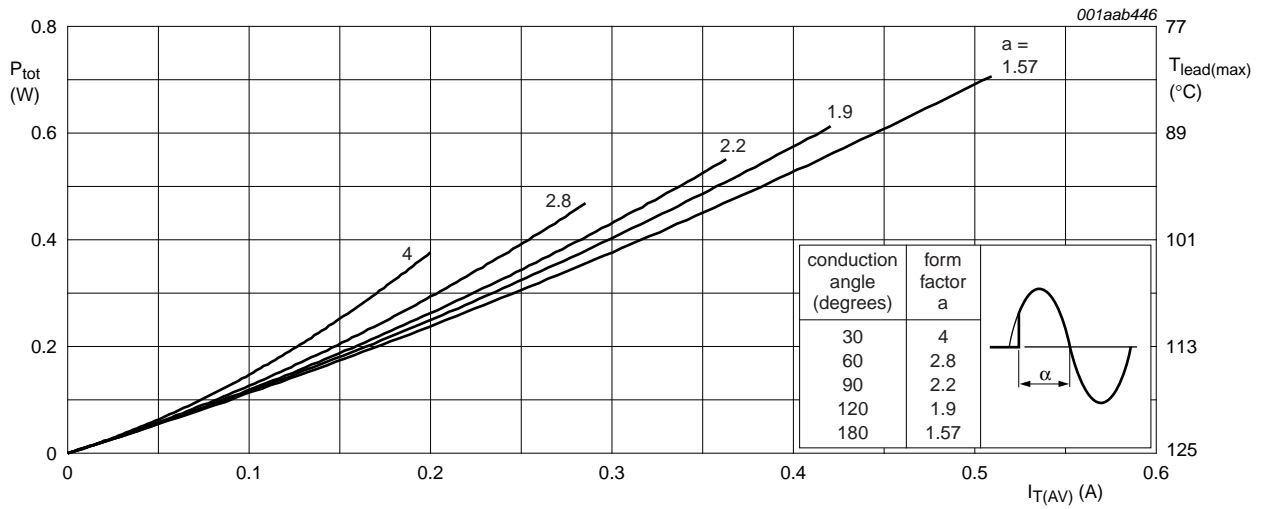
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|--|--|-------|------|-------------|
| V_{DRM}, V_{RRM} | repetitive peak off-state voltages | | | | |
| | BT169B | | [1] - | 200 | V |
| | BT169D | | [1] - | 400 | V |
| | BT169G | | [1] - | 600 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave; $T_{lead} \leq 83\text{ °C}$; see Figure 1 | - | 0.5 | A |
| $I_{T(RMS)}$ | RMS on-state current | all conduction angles; see Figure 4 and 5 | - | 0.8 | A |
| I_{TSM} | non-repetitive peak on-state current | half sine wave; $T_j = 25\text{ °C}$ prior to surge; see Figure 2 and 3 | | | |
| | | $t = 10\text{ ms}$ | - | 8 | A |
| | | $t = 8.3\text{ ms}$ | - | 9 | A |
| I^2t | I^2t for fusing | $t = 10\text{ ms}$ | - | 0.32 | A^2s |
| di_T/dt | repetitive rate of rise of on-state current after triggering | $I_{TM} = 2\text{ A}$; $I_G = 10\text{ mA}$; $di_G/dt = 100\text{ mA}/\mu s$ | - | 50 | $A/\mu s$ |
| I_{GM} | peak gate current | | - | 1 | A |
| V_{GM} | peak gate voltage | | - | 5 | V |
| V_{RGM} | peak reverse gate voltage | | - | 5 | V |
| P_{GM} | peak gate power | | - | 2 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.1 | W |
| T_{stg} | storage temperature | | -40 | +150 | $^{\circ}C$ |
| T_j | junction temperature | | - | 125 | $^{\circ}C$ |

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .



$a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$.

Fig 1. Total power dissipation as a function of average on-state current; maximum values.

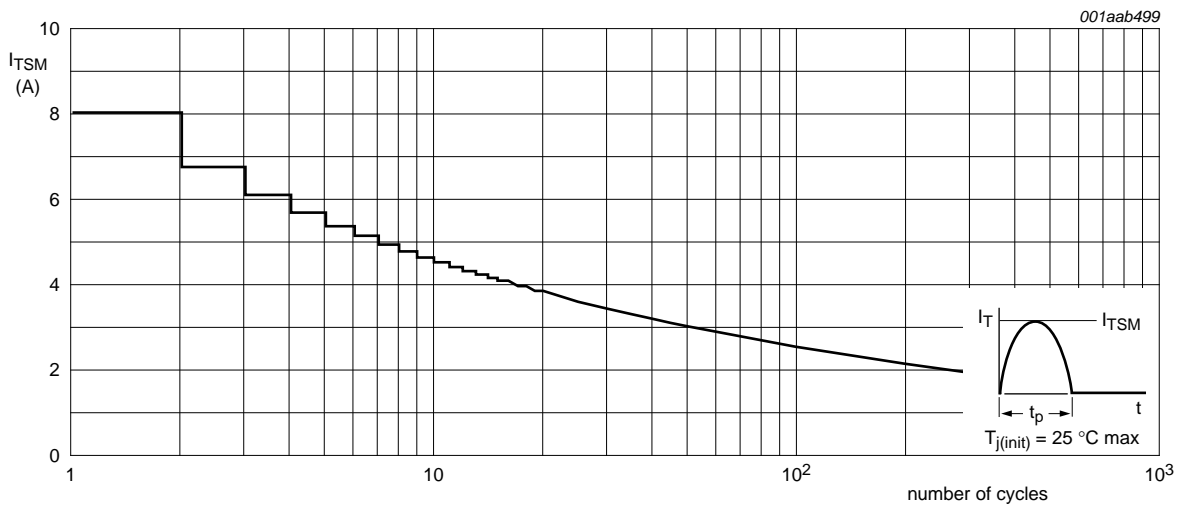
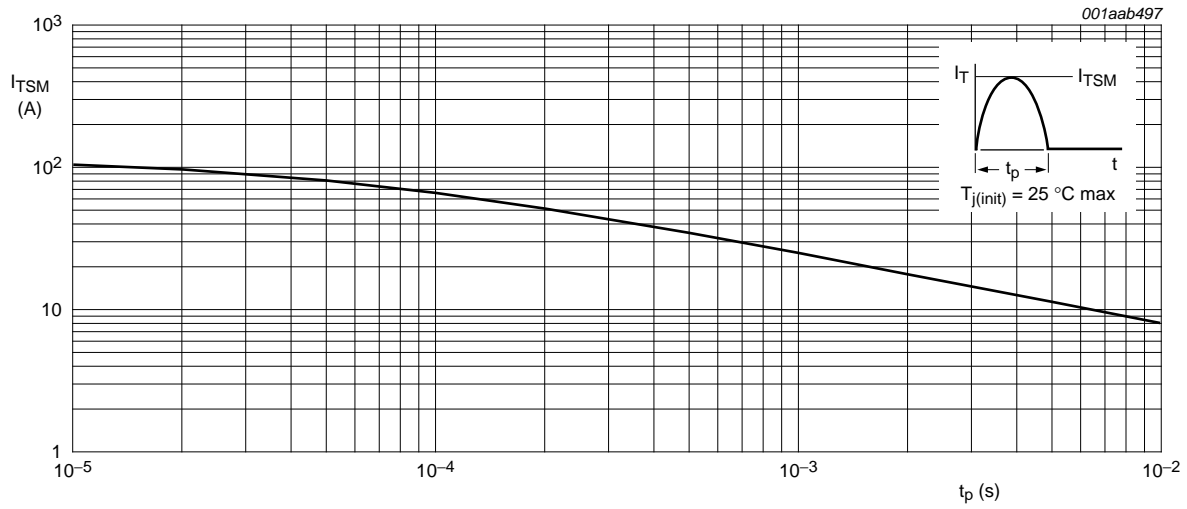
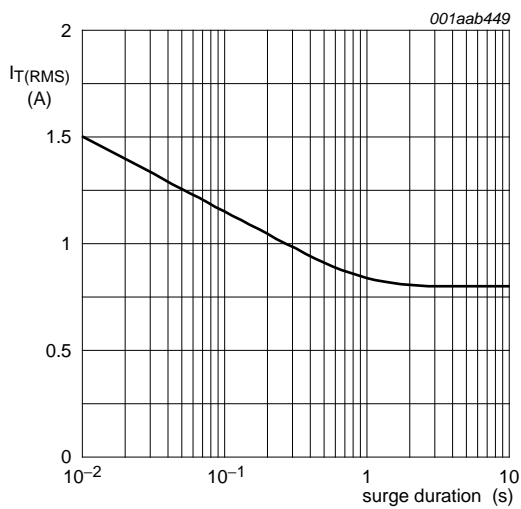


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values.



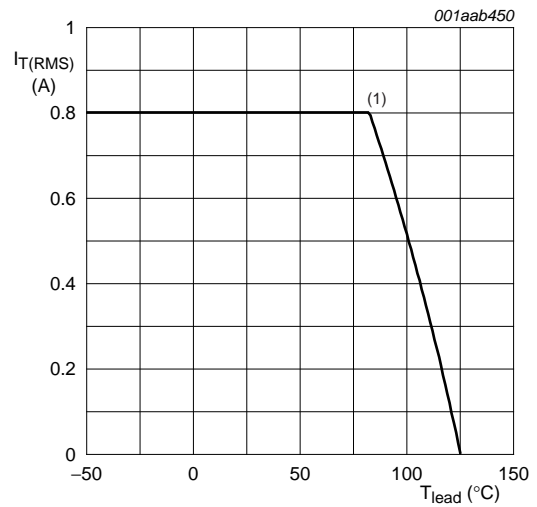
$t_p \leq 10\text{ ms}$.

Fig 3. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values.



$f = 50\text{ Hz}$; $T_{lead} \leq 83\text{ °C}$.

Fig 4. RMS on-state current as a function of surge duration for sinusoidal currents.



(1) $T_{lead} = 83\text{ °C}$.

Fig 5. RMS on-state current as a function of lead temperature; maximum values.

5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---|--|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead | | - | - | 60 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | printed-circuit board mounted; lead length = 4 mm | - | 150 | - | K/W |

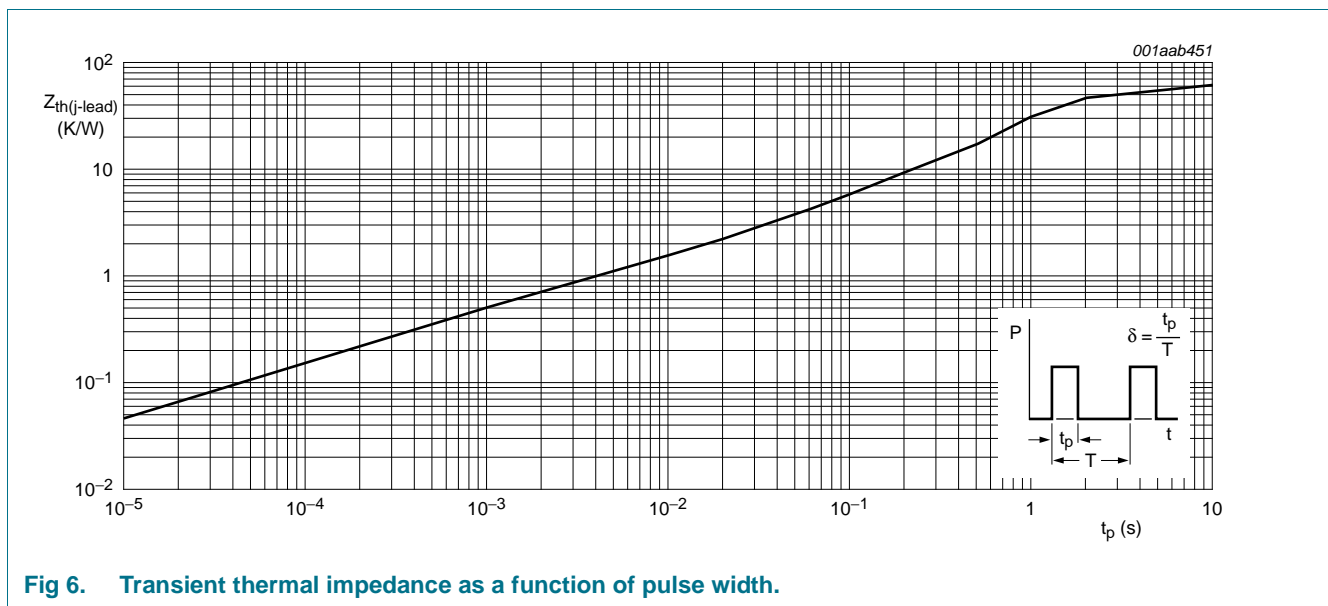


Fig 6. Transient thermal impedance as a function of pulse width.

6. Characteristics

Table 5. Characteristics

$T_j = 25\text{ °C}$ unless otherwise stated.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|--|-----|------|-----|------------------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; gate open circuit; see Figure 8 | - | 50 | 200 | μA |
| I_L | latching current | $V_D = 12\text{ V}$; $I_{GT} = 0.5\text{ mA}$; $R_{GK} = 1\text{ k}\Omega$; see Figure 10 | - | 2 | 6 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $I_{GT} = 0.5\text{ mA}$; $R_{GK} = 1\text{ k}\Omega$; see Figure 11 | - | 2 | 5 | mA |
| V_T | on-state voltage | $I_T = 1.2\text{ A}$ | - | 1.25 | 1.7 | V |
| V_{GT} | gate trigger voltage | $I_T = 10\text{ mA}$; gate open circuit; see Figure 7 | - | - | - | - |
| | | $V_D = 12\text{ V}$ | - | 0.5 | 0.8 | V |
| | | $V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$ | 0.2 | 0.3 | - | V |
| I_D, I_R | off-state leakage current | $V_D = V_{DRM(max)}$; $V_R = V_{RRM(max)}$; $T_j = 125\text{ °C}$; $R_{GK} = 1\text{ k}\Omega$ | - | 0.05 | 0.1 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | critical rate of rise of off-state voltage | $V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ °C}$; exponential waveform; see Figure 12 | - | - | - | - |
| | | $R_{GK} = 1\text{ k}\Omega$ | 500 | 800 | - | $\text{V}/\mu\text{s}$ |
| | | gate open circuit | - | 25 | - | $\text{V}/\mu\text{s}$ |
| t_{gt} | gate controlled turn-on time | $I_{TM} = 2\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 10\text{ mA}$; $dI_G/dt = 0.1\text{ A}/\mu\text{s}$ | - | 2 | - | μs |
| t_q | circuit commuted turn-off time | $V_D = 67\% V_{DRM(max)}$; $T_j = 125\text{ °C}$; $I_{TM} = 1.6\text{ A}$; $V_R = 35\text{ V}$; $dI_{TM}/dt = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 2\text{ V}/\mu\text{s}$; $R_{GK} = 1\text{ k}\Omega$ | - | 100 | - | μs |

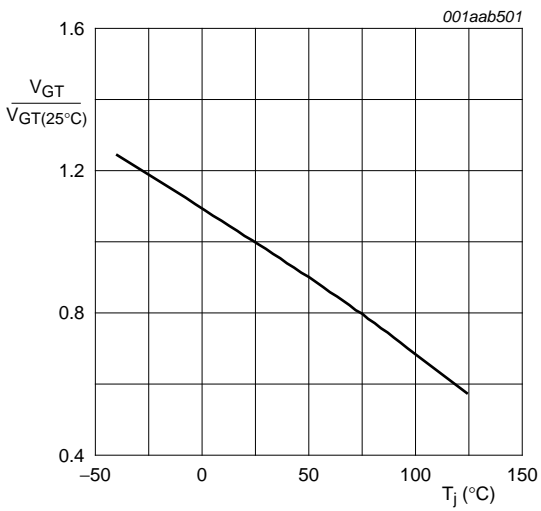


Fig 7. Normalized gate trigger voltage as a function of junction temperature.

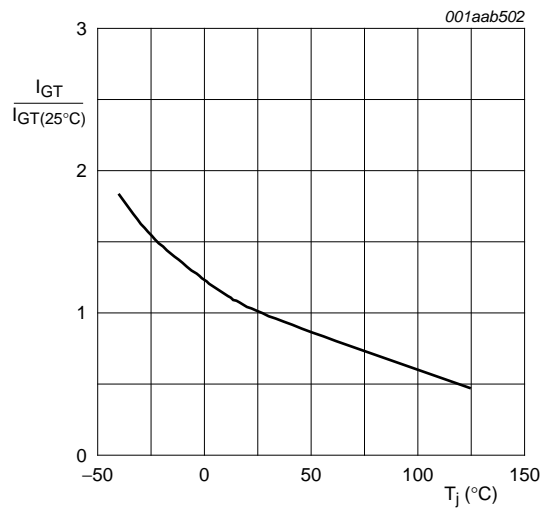
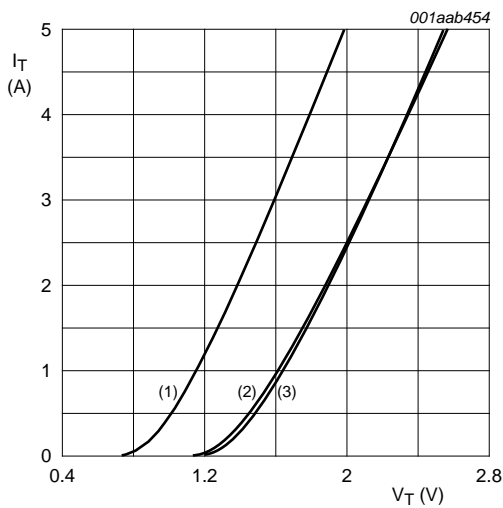
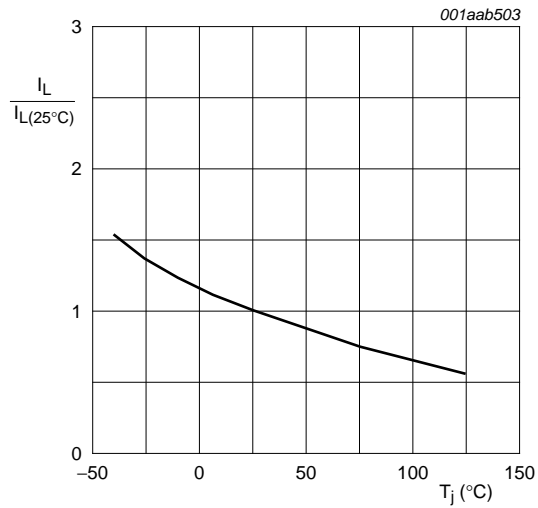


Fig 8. Normalized gate trigger current as a function of junction temperature.



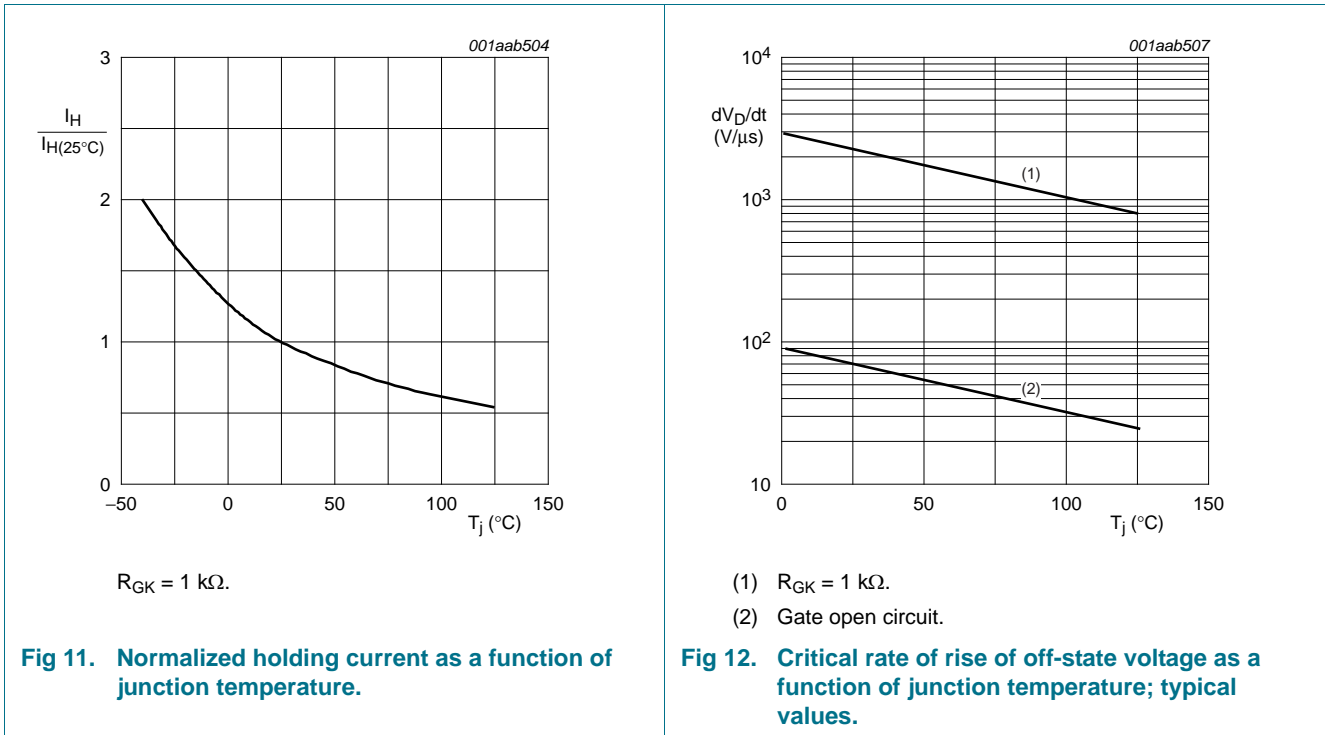
$V_O = 1.067 \text{ V.}$
 $R_S = 0.187 \text{ }\Omega.$
 (1) $T_j = 125 \text{ }^\circ\text{C;}$ typical values.
 (2) $T_j = 125 \text{ }^\circ\text{C;}$ maximum values.
 (3) $T_j = 25 \text{ }^\circ\text{C;}$ maximum values.

Fig 9. On-state current characteristics.



$R_{GK} = 1 \text{ k}\Omega.$

Fig 10. Normalized latching current as a function of junction temperature.



7. Package information

Epoxy meets requirements of UL94 V-0 at 1/8 inch.

8. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

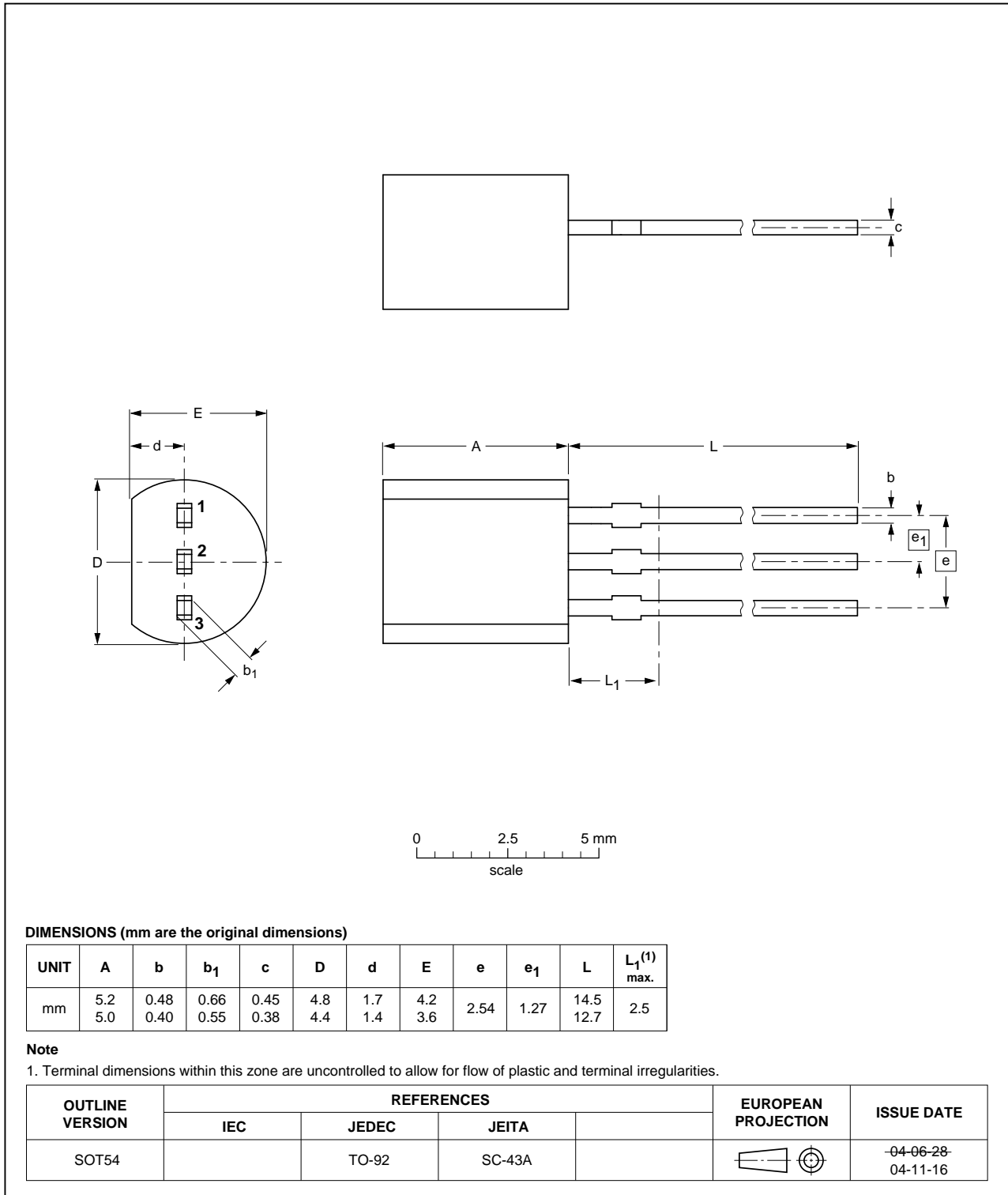


Fig 13. Package outline SOT54 (TO-92).

9. Revision history

Table 6. Revision history

| Document ID | Release date | Data sheet status | Change notice | Order number | Supersedes |
|------------------|---|-----------------------|---------------|----------------|------------------|
| BT169_SERIES v.5 | 20110930 | Product data sheet | - | 9397 750 13512 | BT169_SERIES v.4 |
| Modifications: | <ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. | | | | |
| BT169_SERIES v.4 | 20040823 | Product data sheet | - | 9397 750 13512 | BT169_SERIES v.3 |
| Modifications: | <ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors. Section 1.4 "Quick reference data": BT169E obsolete, removed from list. Table 2 "Ordering information": BT169E obsolete, removed from table. Table 3 "Limiting values": BT169E obsolete, removed from table. | | | | |
| BT169_SERIES v.3 | 20010902 | Product specification | - | not applicable | BT169_SERIES v.2 |
| BT169_SERIES v.2 | 20010901 | Product specification | - | not applicable | BT169_SERIES v.1 |
| BT169_SERIES v.1 | 19970901 | Product specification | - | not applicable | - |

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| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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